

Kazuhito Tsukagoshi

List of Publications by Year in descending order

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373
papers

14,180
citations

17405

63
h-index

28224

105
g-index

381
all docs

381
docs citations

381
times ranked

15196
citing authors

#	ARTICLE	IF	CITATIONS
1	Coherent transport of electron spin in a ferromagnetically contacted carbon nanotube. <i>Nature</i> , 1999, 401, 572-574.	13.7	743
2	Charge transport and mobility engineering in two-dimensional transition metal chalcogenide semiconductors. <i>Chemical Society Reviews</i> , 2016, 45, 118-151.	18.7	423
3	Ambipolar MoTe ₂ Transistors and Their Applications in Logic Circuits. <i>Advanced Materials</i> , 2014, 26, 3263-3269.	11.1	388
4	Solution-Processable Organic Single Crystals with Bandlike Transport in Field-Effect Transistors. <i>Advanced Materials</i> , 2011, 23, 523-526.	11.1	348
5	Quantitative Raman Spectrum and Reliable Thickness Identification for Atomic Layers on Insulating Substrates. <i>ACS Nano</i> , 2012, 6, 7381-7388.	7.3	322
6	Simple and Scalable Gel-Based Separation of Metallic and Semiconducting Carbon Nanotubes. <i>Nano Letters</i> , 2009, 9, 1497-1500.	4.5	307
7	Thickness-Dependent Interfacial Coulomb Scattering in Atomically Thin Field-Effect Transistors. <i>Nano Letters</i> , 2013, 13, 3546-3552.	4.5	285
8	Low-Cost Fully Transparent Ultraviolet Photodetectors Based on Electrospun ZnO/SnO ₂ Heterojunction Nanofibers. <i>Advanced Materials</i> , 2013, 25, 4625-4630.	11.1	275
9	Strong Enhancement of Raman Scattering from a Bulk-Inactive Vibrational Mode in Few-Layer MoTe ₂ . <i>ACS Nano</i> , 2014, 8, 3895-3903.	7.3	275
10	High-performance top-gated monolayer SnS ₂ field-effect transistors and their integrated logic circuits. <i>Nanoscale</i> , 2013, 5, 9666.	2.8	269
11	Self-Limiting Layer-by-Layer Oxidation of Atomically Thin WSe ₂ . <i>Nano Letters</i> , 2015, 15, 2067-2073.	4.5	204
12	Direct evaluation of low-field mobility and access resistance in pentacene field-effect transistors. <i>Journal of Applied Physics</i> , 2010, 107, .	1.1	181
13	Improvement of subthreshold current transport by contact interface modification in p-type organic field-effect transistors. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	164
14	In-Crystal and Surface Charge Transport of Electric-Field-Induced Carriers in Organic Single-Crystal Semiconductors. <i>Physical Review Letters</i> , 2007, 98, 196804.	2.9	161
15	Ambipolar-transporting coaxial nanotubes with a tailored molecular graphene-fullerene heterojunction. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2009, 106, 21051-21056.	3.3	161
16	Origin of the relatively low transport mobility of graphene grown through chemical vapor deposition. <i>Scientific Reports</i> , 2012, 2, 337.	1.6	159
17	Hall Effect of Quasi-Hole Gas in Organic Single-Crystal Transistors. <i>Japanese Journal of Applied Physics</i> , 2005, 44, L1393-L1396.	0.8	154
18	Thickness Scaling Effect on Interfacial Barrier and Electrical Contact to Two-Dimensional MoS ₂ Layers. <i>ACS Nano</i> , 2014, 8, 12836-12842.	7.3	149

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19	Charge injection process in organic field-effect transistors. Applied Physics Letters, 2007, 91, .	1.5	140
20	Carbon nanotube devices for nanoelectronics. Physica B: Condensed Matter, 2002, 323, 107-114.	1.3	138
21	Evaluation of Spin Hall Angle and Spin Diffusion Length by Using Spin Current-Induced Ferromagnetic Resonance. Applied Physics Express, 2012, 5, 073002.	1.1	138
22	Contact-metal dependent current injection in pentacene thin-film transistors. Applied Physics Letters, 2007, 91, .	1.5	137
23	Self-Limiting Oxides on WSe_2 as Controlled Surface Acceptors and Low-Resistance Hole Contacts. Nano Letters, 2016, 16, 2720-2727.	4.5	131
24	Modification of the electric conduction at the pentacene/SiO ₂ interface by surface termination of SiO ₂ . Applied Physics Letters, 2005, 86, 103502.	1.5	130
25	Highly enhanced charge injection in thienoacene-based organic field-effect transistors with chemically doped contact. Applied Physics Letters, 2012, 100, .	1.5	130
26	High-performance transparent flexible transistors using carbon nanotube films. Applied Physics Letters, 2006, 88, 033511.	1.5	123
27	Influence of Disorder on Conductance in Bilayer Graphene under Perpendicular Electric Field. Nano Letters, 2010, 10, 3888-3892.	4.5	116
28	Electrostatically Reversible Polarity of Ambipolar \pm -MoTe ₂ Transistors. ACS Nano, 2015, 9, 5976-5983.	7.3	113
29	Direct observation of contact and channel resistance in pentacene four-terminal thin-film transistor patterned by laser ablation method. Applied Physics Letters, 2004, 84, 813-815.	1.5	105
30	Low Operating Bias and Matched Input/Output Characteristics in Graphene Logic Inverters. Nano Letters, 2010, 10, 2357-2362.	4.5	105
31	Controlled Self-Assembly of Organic Semiconductors for Solution-Based Fabrication of Organic Field-Effect Transistors. Advanced Materials, 2012, 24, 299-306.	11.1	104
32	Effects of dopants in InOx-based amorphous oxide semiconductors for thin-film transistor applications. Applied Physics Letters, 2013, 103, .	1.5	103
33	Introducing Nonuniform Strain to Graphene Using Dielectric Nanopillars. Applied Physics Express, 2011, 4, 075102.	1.1	101
34	Double resonance Raman modes in monolayer and few-layer $MoTe_2$. Physical Review B, 2015, 91, .	1.1	99
35	Surface selective deposition of molecular semiconductors for solution-based integration of organic field-effect transistors. Applied Physics Letters, 2009, 94, .	1.5	96
36	Correlation between grain size and device parameters in pentacene thin film transistors. Applied Physics Letters, 2008, 93, .	1.5	93

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37	Flexible SnO ₂ hollow nanosphere film based high-performance ultraviolet photodetector. Chemical Communications, 2013, 49, 3739.	2.2	93
38	High-density electrostatic carrier doping in organic single-crystal transistors with polymer gel electrolyte. Applied Physics Letters, 2006, 88, 112102.	1.5	91
39	Bias stress instability in pentacene thin film transistors: Contact resistance change and channel threshold voltage shift. Applied Physics Letters, 2008, 92, 063305.	1.5	90
40	Control of Carrier Density by a Solution Method in Carbon-Nanotube Devices. Advanced Materials, 2005, 17, 2430-2434.	11.1	89
41	Site-Selection in Single-Molecule Junction for Highly Reproducible Molecular Electronics. Journal of the American Chemical Society, 2016, 138, 1294-1300.	6.6	88
42	Solution-processed, Self-organized Organic Single Crystal Arrays with Controlled Crystal Orientation. Scientific Reports, 2012, 2, 393.	1.6	87
43	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. Applied Physics Express, 2013, 6, 075101.	1.1	83
44	Stable amorphous In ₂ O ₃ -based thin-film transistors by incorporating SiO ₂ to suppress oxygen vacancies. Applied Physics Letters, 2014, 104, .	1.5	83
45	Spin-dependent boundary resistance in the lateral spin-valve structure. Applied Physics Letters, 2004, 85, 3501-3503.	1.5	82
46	Determination of the Number of Graphene Layers: Discrete Distribution of the Secondary Electron Intensity Stemming from Individual Graphene Layers. Applied Physics Express, 2010, 3, 095101.	1.1	81
47	Low-temperature processable amorphous In-W-O thin-film transistors with high mobility and stability. Applied Physics Letters, 2014, 104, 152103.	1.5	79
48	Inter-Layer Screening Length to Electric Field in Thin Graphite Film. Applied Physics Express, 0, 1, 034007.	1.1	78
49	Charge trapping induced current instability in pentacene thin film transistors: Trapping barrier and effect of surface treatment. Applied Physics Letters, 2008, 93, .	1.5	78
50	Conduction Tuning of Graphene Based on Defect-Induced Localization. ACS Nano, 2013, 7, 5694-5700.	7.3	78
51	Polarization measurements in tip-enhanced Raman spectroscopy applied to single-walled carbon nanotubes. Chemical Physics Letters, 2005, 410, 136-141.	1.2	77
52	Direct observation of the electronic states of single crystalline rubrene under ambient condition by photoelectron yield spectroscopy. Applied Physics Letters, 2008, 93, 173305.	1.5	76
53	Wafer-scale and deterministic patterned growth of monolayer MoS ₂ via liquid-solid method. Nanoscale, 2019, 11, 16122-16129.	2.8	76
54	Selective organization of solution-processed organic field-effect transistors. Applied Physics Letters, 2008, 92, .	1.5	74

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55	Gate control of spin transport in multilayer graphene. <i>Applied Physics Letters</i> , 2008, 92, 212110.	1.5	72
56	Origin of Noise in Layered MoTe ₂ Transistors and its Possible Use for Environmental Sensors. <i>Advanced Materials</i> , 2015, 27, 6612-6619.	11.1	72
57	Carrier Polarity Control in $\hat{\pm}$ -MoTe ₂ Schottky Junctions Based on Weak Fermi-Level Pinning. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 14732-14739.	4.0	72
58	On Practical Charge Injection at the Metal/Organic Semiconductor Interface. <i>Scientific Reports</i> , 2013, 3, 1026.	1.6	71
59	Understanding contact behavior in organic thin film transistors. <i>Applied Physics Letters</i> , 2010, 97, 063307.	1.5	70
60	Large plate-like organic crystals from direct spin-coating for solution-processed field-effect transistor arrays with high uniformity. <i>Organic Electronics</i> , 2012, 13, 264-272.	1.4	69
61	Suppression of thermally activated carrier transport in atomically thin MoS ₂ on crystalline hexagonal boron nitride substrates. <i>Nanoscale</i> , 2013, 5, 9572.	2.8	69
62	Reversible and Precisely Controllable p/n-type Doping of MoTe ₂ Transistors through Electrothermal Doping. <i>Advanced Materials</i> , 2018, 30, e1706995.	11.1	68
63	Boost Up Carrier Mobility for Ferroelectric Organic Transistor Memory via Buffering Interfacial Polarization Fluctuation. <i>Scientific Reports</i> , 2014, 4, 7227.	1.6	67
64	Tunable Doping of Rhenium and Vanadium into Transition Metal Dichalcogenides for Two-dimensional Electronics. <i>Advanced Science</i> , 2021, 8, e2004438.	5.6	66
65	Gate-Voltage Dependence of Zero-Bias Anomalies in Multiwall Carbon Nanotubes. <i>Physical Review Letters</i> , 2004, 92, 036801.	2.9	65
66	Solution-processed organic crystals for field-effect transistor arrays with smooth semiconductor/dielectric interface on paper substrates. <i>Organic Electronics</i> , 2012, 13, 815-819.	1.4	65
67	Barrier inhomogeneities at vertically stacked graphene-based heterostructures. <i>Nanoscale</i> , 2014, 6, 795-799.	2.8	64
68	Strain-induced superconductor/insulator transition and field effect in a thin single crystal of molecular conductor. <i>Applied Physics Letters</i> , 2008, 92, 243508.	1.5	63
69	Current transport in short channel top-contact pentacene field-effect transistors investigated with the selective molecular doping technique. <i>Applied Physics Letters</i> , 2007, 90, 193507.	1.5	62
70	Self-assembly of semiconductor/insulator interfaces in one-step spin-coating: a versatile approach for organic field-effect transistors. <i>Physical Chemistry Chemical Physics</i> , 2013, 15, 7917.	1.3	59
71	Thin-film transistors fabricated by low-temperature process based on Ga- and Zn-free amorphous oxide semiconductor. <i>Applied Physics Letters</i> , 2013, 102, .	1.5	59
72	Proximity effect in a superconductor-metallofullerene-superconductor molecular junction. <i>Physical Review B</i> , 2005, 72, .	1.1	58

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73	Optimal Structure for High-Performance and Low-Contact-Resistance Organic Field-Effect Transistors Using Contact-Doped Coplanar and Pseudo-Staggered Device Architectures. <i>Advanced Functional Materials</i> , 2012, 22, 4577-4583.	7.8	57
74	Dopant selection for control of charge carrier density and mobility in amorphous indium oxide thin-film transistors: Comparison between Si- and W-dopants. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	56
75	Frequency response analysis of pentacene thin-film transistors with low impedance contact by interface molecular doping. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	55
76	Direct formation of organic semiconducting single crystals by solvent vapor annealing on a polymer base film. <i>Journal of Materials Chemistry</i> , 2012, 22, 8462.	6.7	55
77	High-yield production of single-wall carbon nanotubes in nitrogen gas. <i>Chemical Physics Letters</i> , 2003, 372, 45-50.	1.2	54
78	Suppression of short channel effect in organic thin film transistors. <i>Applied Physics Letters</i> , 2007, 91, .	1.5	53
79	Structure and transport properties of the interface between CVD-grown graphene domains. <i>Nanoscale</i> , 2014, 6, 7288.	2.8	52
80	Field-Induced Carrier Delocalization in the Strain-Induced Mott Insulating State of an Organic Superconductor. <i>Physical Review Letters</i> , 2009, 103, 116801.	2.9	49
81	Magnetotransport through disordered and anisotropic antidot lattices in GaAs/Al _x Ga _{1-x} As heterostructures. <i>Physical Review B</i> , 1995, 52, 8344-8347.	1.1	46
82	A Reliable Method for Fabricating sub-10 nm Gap Junctions Without Using Electron Beam Lithography. <i>E-Journal of Surface Science and Nanotechnology</i> , 2003, 1, 41-44.	0.1	46
83	Self-Assembly Atomic Stacking Transport Layer of 2D Layered Titania for Perovskite Solar Cells with Extended UV Stability. <i>Advanced Energy Materials</i> , 2018, 8, 1701722.	10.2	46
84	Electron transport in metal/multiwall carbon nanotube/metal structures (metal=Ti or Pt/Au). <i>Applied Physics Letters</i> , 2001, 79, 1354-1356.	1.5	45
85	Patterning solution-processed organic single-crystal transistors with high device performance. <i>AIP Advances</i> , 2011, 1, .	0.6	45
86	Origin of low-frequency noise in pentacene field-effect transistors. <i>Solid-State Electronics</i> , 2011, 61, 106-110.	0.8	45
87	Complementary-Like Graphene Logic Gates Controlled by Electrostatic Doping. <i>Small</i> , 2011, 7, 1552-1556.	5.2	45
88	Rational design of a high performance all solid state flexible micro-supercapacitor on paper. <i>RSC Advances</i> , 2013, 3, 15827.	1.7	45
89	Solution-assembled nanowires for high performance flexible and transparent solar-blind photodetectors. <i>Journal of Materials Chemistry C</i> , 2015, 3, 596-600.	2.7	45
90	Fabrication of WO ₃ electrochromic devices using electro-exploding wire techniques and spray coating. <i>Solar Energy Materials and Solar Cells</i> , 2021, 223, 110960.	3.0	45

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91	Pentacene nanotransistor with carbon nanotube electrodes. Applied Physics Letters, 2004, 85, 1021-1023.	1.5	44
92	Molecular-packing-enhanced charge transport in organic field-effect transistors based on semiconducting porphyrin crystals. Applied Physics Letters, 2007, 91, 123501.	1.5	43
93	Carrier mobility in organic field-effect transistors. Journal of Applied Physics, 2011, 110, 104513.	1.1	43
94	Volatile/Nonvolatile Dual-Functional Atom Transistor. Applied Physics Express, 2011, 4, 015204.	1.1	42
95	Quantum dots in carbon nanotubes. Semiconductor Science and Technology, 2006, 21, S52-S63.	1.0	41
96	Enhanced Logic Performance with Semiconducting Bilayer Graphene Channels. ACS Nano, 2011, 5, 500-506.	7.3	40
97	Spin transport in nanotubes (invited). Journal of Applied Physics, 2001, 89, 6863-6867.	1.1	39
98	Interface modification of a pentacene field-effect transistor with a submicron channel. Applied Physics Letters, 2006, 89, 113507.	1.5	39
99	Forming semiconductor/dielectric double layers by one-step spin-coating for enhancing the performance of organic field-effect transistors. Organic Electronics, 2012, 13, 1146-1151.	1.4	39
100	Patterning technology for solution-processed organic crystal field-effect transistors. Science and Technology of Advanced Materials, 2014, 15, 024203.	2.8	39
101	Pentacene transistor encapsulated by poly-para-xylylene behaving as gate dielectric insulator and passivation film. Applied Physics Letters, 2005, 87, 183502.	1.5	38
102	Pronounced photogating effect in atomically thin WSe ₂ with a self-limiting surface oxide layer. Applied Physics Letters, 2018, 112, .	1.5	38
103	All-Solution-Processed Selective Assembly of Flexible Organic Field-Effect Transistor Arrays. Applied Physics Express, 2010, 3, 051601.	1.1	37
104	Reduction of charge injection barrier by 1-nm contact oxide interlayer in organic field effect transistors. Applied Physics Letters, 2012, 100, .	1.5	37
105	High-performance organic field-effect transistors based on dihexyl-substituted dibenzo[d,h]thieno[3,2-b;4,5-b']dithiophene. Journal of Materials Chemistry, 2012, 22, 7715.	6.7	37
106	In situ purification to eliminate the influence of impurities in solution-processed organic crystals for transistor arrays. Journal of Materials Chemistry C, 2013, 1, 1352-1358.	2.7	37
107	Modulation of effective damping constant using spin Hall effect. Applied Physics Letters, 2014, 104, 092408.	1.5	37
108	Solvent-Mediated Shape Engineering of Fullerene (C ₆₀) Polyhedral Microcrystals. Chemistry of Materials, 2018, 30, 7146-7153.	3.2	37

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109	Current distribution inside Py-Culateral spin-valve devices. Physical Review B, 2005, 71, .	1.1	36
110	A search for multiplicity fluctuations in high energy nucleus-nucleus collisions. Physics Letters, Section B: Nuclear, Elementary Particle and High-Energy Physics, 1990, 252, 303-310.	1.5	35
111	Suppression of spin accumulation in nonmagnet due to ferromagnetic ohmic contact. Applied Physics Letters, 2004, 85, 3795-3796.	1.5	35
112	Transition-Voltage Method for Estimating Contact Resistance in Organic Thin-Film Transistors. IEEE Electron Device Letters, 2010, 31, 509-511.	2.2	35
113	Performance Enhancement of Thin-Film Transistors by Using High-Purity Semiconducting Single-Wall Carbon Nanotubes. Applied Physics Express, 0, 2, 071601.	1.1	33
114	Operation of logic function in a Coulomb blockade device. Applied Physics Letters, 1998, 73, 2515-2517.	1.5	32
115	Gate capacitance in electrochemical transistor of single-walled carbon nanotube. Applied Physics Letters, 2006, 88, 073104.	1.5	32
116	Identifying the molecular adsorption site of a single molecule junction through combined Raman and conductance studies. Chemical Science, 2019, 10, 6261-6269.	3.7	32
117	Resistance modulation of multilayer graphene controlled by the gate electric field. Semiconductor Science and Technology, 2010, 25, 034008.	1.0	30
118	Unravelling the origin of the photocarrier dynamics of fullerene-derivative passivation of SnO ₂ electron transporters in perovskite solar cells. Journal of Materials Chemistry A, 2020, 8, 23607-23616.	5.2	30
119	Anisotropic transport in graphene on SiC substrate with periodic nanofacets. Applied Physics Letters, 2010, 96, 062111.	1.5	29
120	Strain-Tunable Superconducting Field-Effect Transistor with an Organic Strongly-Correlated Electron System. Advanced Materials, 2014, 26, 3490-3495.	11.1	29
121	On/Off Boundary of Photocatalytic Activity between Single- and Bilayer MoS ₂ . ACS Nano, 2020, 14, 6663-6672.	7.3	29
122	Coulomb blockade in multiwalled carbon nanotube island with nanotube leads. Applied Physics Letters, 2001, 79, 1465-1467.	1.5	28
123	Control of device parameters by active layer thickness in organic field-effect transistors. Applied Physics Letters, 2011, 98, .	1.5	28
124	Electric-field-induced Mott transition in an organic molecular crystal. Physical Review B, 2011, 84, .	1.1	28
125	Edge mixing dynamics in graphene p-n junctions in the quantum Hall regime. Nature Communications, 2015, 6, 8066.	5.8	28
126	Catalytic growth of carbon nanotubes and their patterning based on ink-jet and lithographic techniques. Journal of Electroanalytical Chemistry, 2003, 559, 25-30.	1.9	27

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127	Organic light-emitting diode driven by organic thin film transistor on plastic substrates. Journal of Applied Physics, 2006, 99, 064506.	1.1	27
128	Self-powered graphene thermistor. Nano Energy, 2016, 26, 586-594.	8.2	27
129	Fullerene/cobalt porphyrin charge-transfer cocrystals: Excellent thermal stability and high mobility. Nano Research, 2018, 11, 1917-1927.	5.8	27
130	Spin-current-assisted domain-wall depinning in a submicron magnetic wire. Journal of Applied Physics, 2003, 94, 7947.	1.1	26
131	Charge transport of copper phthalocyanine single-crystal field-effect transistors stable above 100Å°C. Applied Physics Letters, 2006, 88, 122110.	1.5	26
132	Suppressed pinning field of a trapped domain wall due to direct current injection. Journal of Applied Physics, 2003, 94, 7266-7269.	1.1	25
133	Purification of Single-Wall Carbon Nanotubes Synthesized from Alcohol by Catalytic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2004, 43, L396-L398.	0.8	25
134	Direct Formation of Micro-/Nanocrystalline 2,5-Dimethyl-N,Nâ€-dicyanoquinonediimine Complexes on SiO2/Si Substrates and Multiprobe Measurement of Conduction Properties. Journal of the American Chemical Society, 2006, 128, 700-701.	6.6	25
135	Influence of electrode size on resistance switching effect in nanogap junctions. Applied Physics Letters, 2010, 97, 073118.	1.5	25
136	Suppression of excess oxygen for environmentally stable amorphous In-Si-O thin-film transistors. Applied Physics Letters, 2015, 106, .	1.5	25
137	Virtual substrate method for nanomaterials characterization. Nature Communications, 2017, 8, 15629.	5.8	25
138	On the Mechanism of Commensurability Oscillations in Anisotropic Antidot Lattices. Journal of the Physical Society of Japan, 1996, 65, 811-817.	0.7	24
139	Extraction of low-frequency noise in contact resistance of organic field-effect transistors. Applied Physics Letters, 2010, 97, .	1.5	24
140	Self-Aligned Formation of Sub 1 nm Gaps Utilizing Electromigration during Metal Deposition. ACS Applied Materials & Interfaces, 2013, 5, 12869-12875.	4.0	23
141	Codoping of zinc and tungsten for practical high-performance amorphous indium-based oxide thin film transistors. Journal of Applied Physics, 2015, 118, .	1.1	23
142	Hunting for Monolayer Oxide Nanosheets and Their Architectures. Scientific Reports, 2016, 6, 19402.	1.6	23
143	Effect of air exposure on metal/organic interface in organic field-effect transistors. Applied Physics Letters, 2011, 98, 243301.	1.5	22
144	Mixed-Salt Enhanced Chemical Vapor Deposition of Two-Dimensional Transition Metal Dichalcogenides. Chemistry of Materials, 2021, 33, 7301-7308.	3.2	22

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145	Spin electronics using carbon nanotubes. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000, 6, 848-851.	1.3	21
146	Modeling of static electrical properties in organic field-effect transistors. <i>Journal of Applied Physics</i> , 2011, 110, 014510.	1.1	21
147	Role of atomic terraces and steps in the electron transport properties of epitaxial graphene grown on SiC. <i>AIP Advances</i> , 2012, 2, .	0.6	21
148	Reducing contact resistance in ferroelectric organic transistors by buffering the semiconductor/dielectric interface. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	21
149	One-Dimensional Fullerene/Porphyrin Cocrystals: Near-Infrared Light Sensing through Component Interactions. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 2878-2883.	4.0	21
150	Nanoscale Coulomb blockade memory and logic devices. <i>Nanotechnology</i> , 2001, 12, 155-159.	1.3	20
151	Temperature-mediated switching of magnetoresistance in Co-contacted multiwall carbon nanotubes. <i>Applied Physics Letters</i> , 2003, 83, 1008-1010.	1.5	20
152	Two-dimensional MoTe ₂ materials: From synthesis, identification, and charge transport to electronics applications. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 1102A1.	0.8	20
153	Formation mechanism of carbon nanotubes in the gas-phase synthesis from colloidal solutions of nanoparticles. <i>Current Applied Physics</i> , 2005, 5, 128-132.	1.1	19
154	Reproducible formation of nanoscale-gap electrodes for single-molecule measurements by combination of FIB deposition and tunneling current detection. <i>Microelectronic Engineering</i> , 2006, 83, 1471-1473.	1.1	19
155	Understanding Thickness-Dependent Charge Transport in Pentacene Transistors by Low-Frequency Noise. <i>IEEE Electron Device Letters</i> , 2013, 34, 1298-1300.	2.2	19
156	Joule's law for organic transistors exploration: Case of contact resistance. <i>Journal of Applied Physics</i> , 2013, 113, 064507.	1.1	19
157	Flexible field-effect transistor arrays with patterned solution-processed organic crystals. <i>AIP Advances</i> , 2013, 3, .	0.6	19
158	Homogeneous double-layer amorphous Si-doped indium oxide thin-film transistors for control of turn-on voltage. <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	19
159	Two-Dimensional Bis(dithiolene)iron(II) Self-Powered UV Photodetectors with Ultrahigh Air Stability. <i>Advanced Science</i> , 2021, 8, 2100564.	5.6	19
160	Influence of edge current and contact on nonlocal Shubnikov-de Haas oscillations in macroscopic GaAs/AlGaAs wire. <i>Solid State Communications</i> , 1991, 80, 571-574.	0.9	18
161	Growth control of pentacene films on SiO ₂ /Si substrates towards formation of flat conduction layers. <i>Thin Solid Films</i> , 2004, 467, 168-171.	0.8	18
162	Contact resistance modulation in carbon nanotube devices investigated by four-probe experiments. <i>Applied Physics Letters</i> , 2006, 88, 053118.	1.5	18

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163	Gate-controlled superconducting proximity effect in ultrathin graphite films. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 1495-1497.	1.3	18
164	Contact resistance instability in pentacene thin film transistors induced by ambient gases. <i>Applied Physics Letters</i> , 2009, 94, 083309.	1.5	18
165	Tunable contact resistance in double-gate organic field-effect transistors. <i>Organic Electronics</i> , 2012, 13, 1583-1588.	1.4	18
166	Liquid phase growth of graphene on silicon carbide. <i>Carbon</i> , 2012, 50, 5076-5084.	5.4	18
167	Current-Direction-Dependent Commensurate Oscillations in GaAs/AlGaAs Antidot Superlattice. <i>Japanese Journal of Applied Physics</i> , 1995, 34, 4335-4337.	0.8	17
168	Electron pump in multiple-tunnel junctions. <i>Physical Review B</i> , 1997, 56, 3972-3975.	1.1	17
169	Charge Transport Properties of Hexabenzocoronene Nanotubes by Field Effect: Influence of the Oligoether Side Chains on the Mobility. <i>Chemistry Letters</i> , 2009, 38, 888-889.	0.7	17
170	Gate-Controlled P _h Junction Switching Device with Graphene Nanoribbon. <i>Applied Physics Express</i> , 2012, 5, 015101.	1.1	17
171	Controlling the crystal formation in solution-process for organic field-effect transistors with high-performance. <i>Organic Electronics</i> , 2012, 13, 2975-2984.	1.4	17
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173	Charge transfer control by gate voltage in crossed nanotube junction. <i>Applied Physics Letters</i> , 2002, 81, 2250-2252.	1.5	16
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